

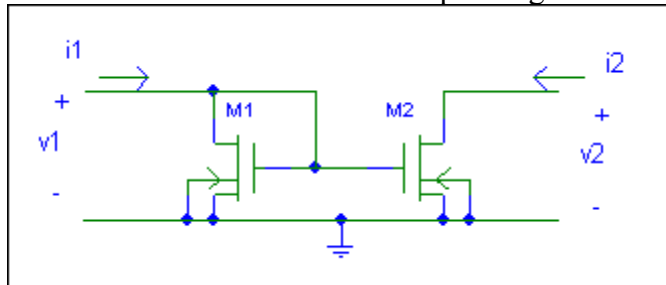
EE 303 Midterm Spring 2008

Open book, open notes. Only signed exam books, certifying all work is your own, will be graded. Be sure to show your reasoning for partial credit & move on if stuck. (75 min.)

When numerical values are requested use the spice parameters $KP=2 \times 10^{-5} \text{A/V}^2$, $W=L=10\mu$, $V_{TO}=0.8\text{V}$, $LAMBDA=2 \times 10^{-3}/\text{V}$, $C_{gs}=C_{gd}=5\text{pF}$, $BF=120$, $V_{AF}=110\text{V}$, $I_S=10^{-14}\text{A}$, $V_{BE}=0.7\text{V}$. For thermal voltage use $V_T=0.026\text{V}$.

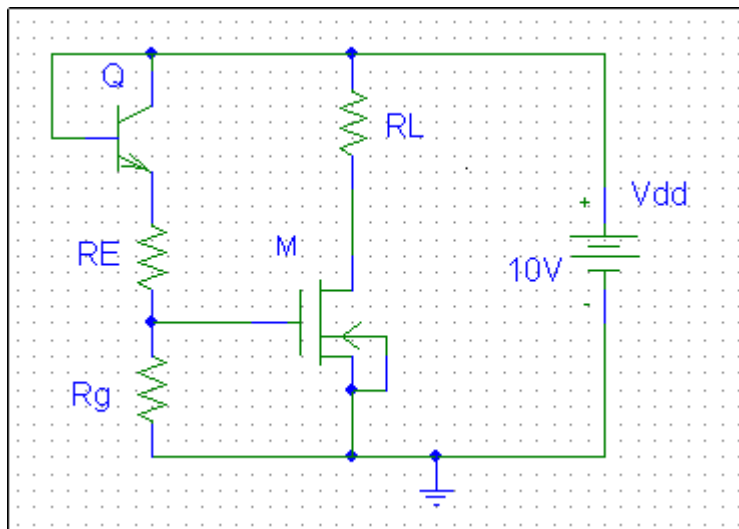
1. (50 points; 30 minutes)

For the following current mirror, assume that at DC the mirror gives $I_2=3\text{mA}$ out for $I_1=3\text{mA}$ in with identical transistors operating in the saturation region.



- draw the small signal 2-port equivalent circuit.
- analytically (not numerically) find the Y matrix in terms of the Spice parameters (including both gate capacitors).
- numerically evaluate $Y(s)$ and comment upon the poles and zeros.
- assuming a load conductance g_L is placed across port 2, analytically find the small signal voltage gain, $(v_2/v_1)=G(s)$. Evaluate $G(s)$ numerically for $g_L=2\text{mMho}$.

2. (50 points; 30 minutes)



For this circuit

- Numerically find R_E and R_g so that the $V_{GS} = 2V$.
- Given the result of part a) find numerically the maximum R_L (call it R_{max}) such that the transistor M remains in saturation for all smaller values of the non-negative load resistance R_L .
- Calculate numerically the drain current, i_D , of M for $0 \leq R_L \leq R_{max}$ and sketch i_D vs R_L .